

S4349

## Quadrant Si PIN photodiode

The S4349 is a quadrant Si PIN photodiode having sensitivity in the UV to near IR spectral range. A quadrant element format allows position sensing such as for laser beam axis alignment.

### Features

- Quadrant (2 × 2) element format
- Low crosstalk: 2% max.
- Wide spectral response range: 190 to 1000 nm
- High-speed response:  $f_c=20$  MHz
- TO-5 metal package

### Applications

- Laser beam axis alignment
- Position sensing

### Structure

Parameter	Symbol	Value	Unit
Window material	-	Quartz glass	-
Photosensitive area	A	□3.0/4 elements	mm
Element gap	-	100	μm

### Absolute maximum ratings

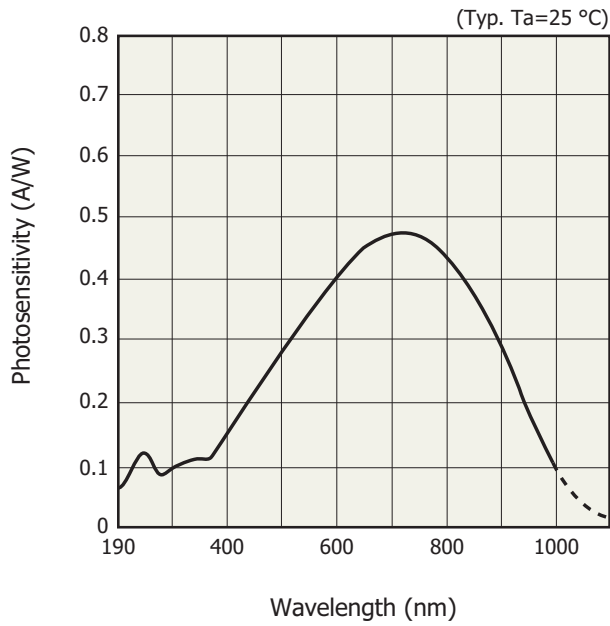
Parameter	Symbol	Value	Unit
Reverse voltage	$V_R$ max	20	V
Operating temperature	$T_{opr}$	-20 to +60	°C
Storage temperature	$T_{stg}$	-55 to +80	°C

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

### Electrical and optical characteristics ( $T_a=25$ °C, per 1 element)

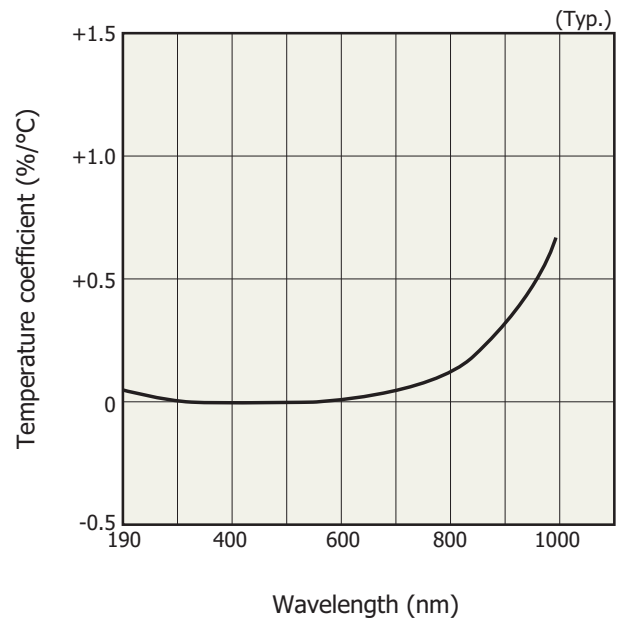
Parameter	Symbol	Condition	Typ.	Max.	Unit
Spectral response range	$\lambda$		190 to 1000	-	nm
Peak sensitivity wavelength	$\lambda_p$		720	-	nm
Photosensitivity	S	$\lambda=\lambda_p$	0.45	-	A/W
Dark current	$I_D$	$V_R=5$ V	0.01	0.2	nA
Temperature coefficient of $I_D$	$T_{CID}$		1.12	-	times/°C
Cutoff frequency	$f_c$	$V_R=5$ V, $R_L=50$ Ω $\lambda=780$ nm, -3 dB	20	-	MHz
Terminal capacitance	$C_t$	$V_R=5$ V, $f=1$ MHz	25	-	pF
Noise equivalent power	NEP	$V_R=5$ V, $\lambda=\lambda_p$	$4.0 \times 10^{-15}$	-	W/Hz <sup>1/2</sup>
Crosstalk	CL	$V_R=5$ V, $\lambda=780$ nm	-	2	%

### Spectral response



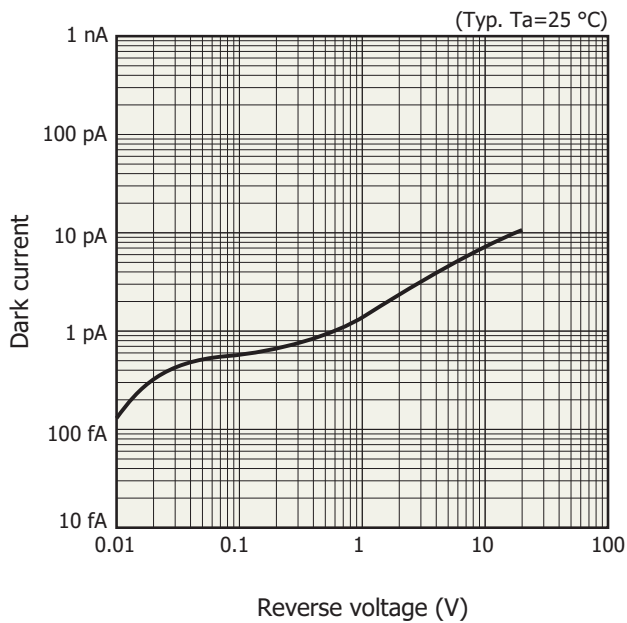
KMPDB0126EA

### Photosensitivity temperature characteristics



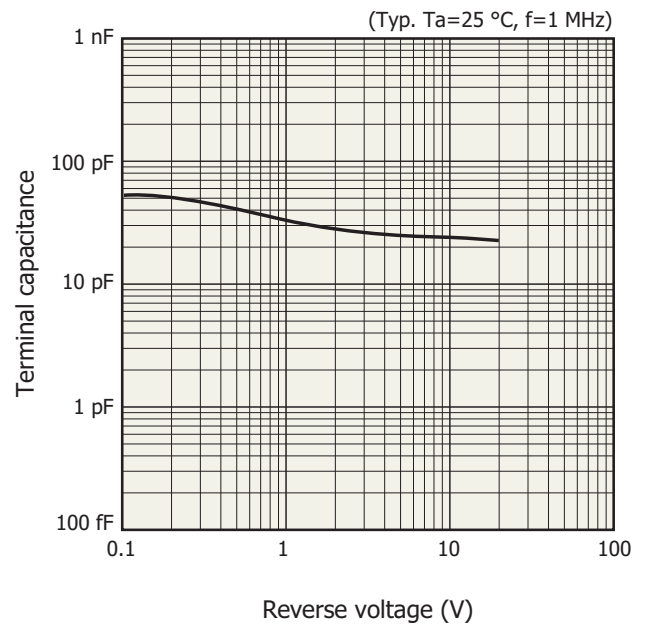
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### Dark current vs. reverse voltage



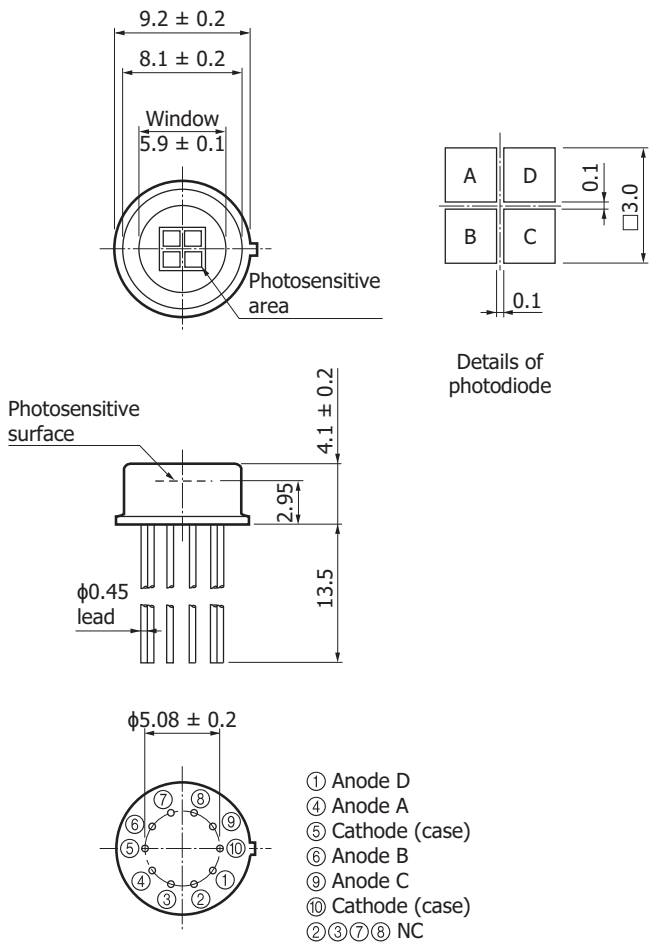
KMPDB0128EA

### Terminal capacitance vs. reverse voltage



KMPDB0129EA

### Dimensional outline (unit: mm)



KMPDA0114EA

### Precautions against UV light exposure

- When UV light irradiation is applied, the product characteristics may degrade. Such examples include degradation of the product's UV sensitivity and increase in dark current. This phenomenon varies depending on the irradiation level, irradiation intensity, usage time, and ambient environment and also varies depending on the product model. Before employing the product, we recommend that you check the tolerance under the ultraviolet light environment that the product will be used in.
- Exposure to UV light may cause the characteristics to degrade due to gas released from the resin bonding the product's component materials. As such, we recommend that you avoid applying UV light directly on the resin and apply it on only the inside of the photosensitive area by using an aperture or the like.

## Related information

[www.hamamatsu.com/sp/ssd/doc\\_en.html](http://www.hamamatsu.com/sp/ssd/doc_en.html)

### ■ Precautions

- Disclaimer
- Metal, ceramic, plastic package products

### ■ Technical information

- Si photodiode/Application circuit examples

Information described in this material is current as of October, 2015.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

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